2388

mot

4K Bit Static Random Access Memory

The MCM6147A is a 4096-bit static random access memory organized as 4096 words by 1-bit, fabricated using Motorola's high performance CMOS silicon gate technology (HCMOS). It uses a design approach which provides the simple timing features associated with fully static memories and the reduced power associated with CMOS memories. This means low power without the need for clocks, nor reduced data rates due to cycle times that exceed access times.

Chip enable (\overline{E}) controls the power-down feature. It is not a clock, but rather a chip control that affects power consumption. After \overline{E} goes high, initiating deselect mode, the part automatically reduces its power requirements and remains in this low-power standby mode as long as \overline{E} remains high.

The MCM6147A is in an 18-pin dual in-line package with the industry standard pin out. It is TTL compatible in all respects. The data out has the same polarity as the input data. A data input and a separate three-state output provide flexibility and allow easy OR-ties.

- Single +5 V Supply
- Fully Static Memory-No Clock or Timing Strobe Required
- Maximum Access Time
 MCM6147A-55 and MCM61L47A-55 = 55 ns
 MCM6147A-70 and MCM61L47A-70 = 70 ns
- Automatic Power Down
- Low Power Supply Current Drain
 35 mA Maximum (Active)
 12 mA Maximum (Standby—TTL Levels)
 800 μA Maximum (Standby—Full Rail, MCM6147A)
 100 μA Maximum (Standby—Full Rail, MCM61L47A)
- Low Standby Power Version Available—MCM61L47A
- Directly TTL Compatible—All Inputs and Output
- Separate Data Input and Three-State Output
- Equal Access and Cycle Time
- High Density 18-Pin Package
- Improved ESD Protection

BLOCK DIAGRAM AΠ PIN 18 = V_{CC} PIN 9 = GND MEMORY ARRAY ROW 64 ROWS SELECT 46 64 COLUMNS . . . $D^{\frac{11}{2}}$ COLUMN I/O CIRCUITS COLUMN SELECT 13 A9 A10 A11 Α5

MCM6147A 040733 MCM61L47A



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PIN	PIN ASSIGNMENT							
A0 [1 •	18 D V _C (3					
A1 [2	17 🗖 🗚 6						
A2 [3	16 🛮 A7						
АЗ [4	15 🕽 A8						
A4 [5	14 🛮 A9						
A5 [6	13 🛭 A11	0					
a C	7	12] A1	1					
₩d	8	11 1 D	•					
v _{SS} C	9	10 DE						

	PIN NAMES					
A0-A11	Address					
Ē	Chip Enable					
D						
α	Data Output					
W						
Vcc · · ·	Power (+5 V)					
V _{SS}	Ground					



ABSOLUTE MAXIMUM RATING (See Note)

Rating	Value	Unit
Temperature Under Bias	- 10 to +85	°C
Voltage on Any Pin with Respect to V _{CC}	-0.5 to +7.0	٧
Power Dissipation	1.0	Watt
Operating Temperature Range	0 to +70	°C
Storage Temperature Range	65 to + 150	°C

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(Full Operating Voltage and Temperature Range Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc Vss	4.5 0	5.0 0	5.5 0	٧
Input High Voltage, All Inputs	V _{IH}	2.0		6.0	V
Input Low Voltage, All Inputs	V _{IL}	-0.3	_	0.8	V

DC CHARACTERISTICS

Parameter		Symbol	Min	Тур*	Max	Unit
Input Load Current (All Input Pins, V _{in} = 0 to 5.5 V)		IIL	ı	0.01	1.0	μА
Output Leakage Current (E=2.0 V, Vout=0 to 5.5 V)		I _{OL}	1	0.1	1.0	μА
Power Supply Current (E=V _{IL} , Output Open)		^I cc	_	15	(35)	mA
Standby Current ($\overline{E} = V_{IH}$)		ISB	_	5	12	mA
Standby Current ($\overline{E} = V_{CC} - 0.2 \text{ V}, 0.2 \text{ V} \ge V_{in} \ge V_{CC} - 0.2 \text{ V}$)	MCM6147A MCM61L47A	^I SB1	_ _	200 25	800	μΑ
Input Low Voltage		V _{IL}	-0.3		0.8	ν
Input High Voltage		V _{IH}	2.0	_	6.0	V
Output Low Voltage (I _{OL} = 12.0 mA)		VOL	_	_	0.4	٧
Output High Voltage** (IOH = -8.0 mA)		VOH	2.4		_	V

^{*}Typical values are for $T_A = 25^{\circ}\text{C}$ and $V_{CC} = 5.0 \text{ V}$.

CAPACITANCE

(f = 1.0 MHz, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Characteristic	Symbol	Max	Unit
Input Capacitance (V _{in} = 0 V)	C _{in}	5.0	pF
Output Capacitance (Vout=0 V)	C _{out}	7.0	pF

Capacitance measured with a Boonton Meter or effective capacitance calculated from the equation: $C = I\Delta_t/\Delta V$.

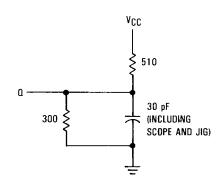


Figure 1. Output Load

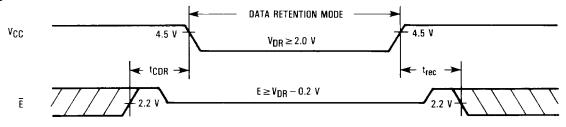
^{**}Output voltages are compatible with Motorola's High-Speed CMOS Logic Family if the same power supply voltage is used.

LOW VCC DATA RETENTION CHARACTERISTICS (T_A = 0 to +70°C) (MCM61L47A Only)

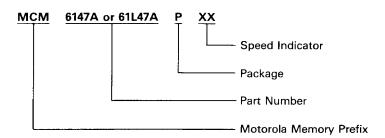
					,	
Parameter	Conditions	Symbol	Min	Тур	Max	Unit
V _{CC} for Data Retention	$\overline{E} \ge V_{CC} - 0.2V$ $V_{in} \ge V_{CC} - 0.2 \text{ V or } V_{in} \le 0.2 \text{ V}$	V _{DR}	2.0	_	_	V
Data Retention Current	$V_{CC} = 3.0 \text{ V}, \ \vec{E} \ge 2.8 \text{ V}$ $V_{in} \ge 2.8 \text{ V} \text{ or } V_{in} \le 0.2 \text{ V}$	ICCDR	_	_	40	μΑ
Chip Disable to Data Retention Time	See Retention Waveform	tCDR	0	_	_	ns
Operation Recovery Time		t _{rec}	*tAVAX	_	_	ns

 $t_{AVAX} = Read Cycle Time.$

LOW VCC DATA RETENTION WAVEFORM



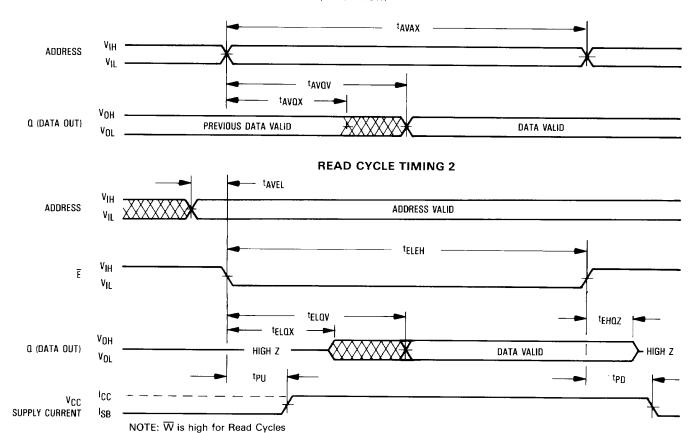
ORDERING INFORMATION (Order by Full Part Number)



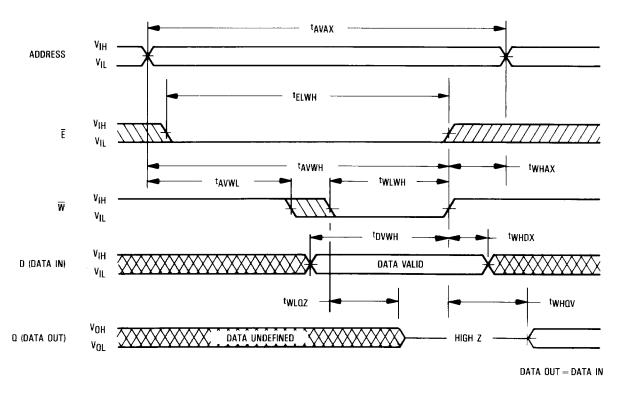
Full Part Numbers — MCM6147AP55 MCM61L47AP55 MCM6147AP70 MCM61L47AP70

READ CYCLE TIMING 1

(E Held Low)



WRITE CYCLE TIMING



AC OPERATING CONDITIONS AND CHARACTERISTICS

(Full Operating Voltage and Temperature Unless Otherwise Noted)

Input Pulse Levels	. 0 Volt to 3.5 Volts	Input and Output Timing Reference Levels	1.5 Volts
Input Rise and Fall Times	10 ns	Output Load	Figure 1

READ, WRITE CYCLES

Parameter	Symbol	MCM6147A-55 MCM61L47A-55		MCM6147A-70 MCM61L47A-70		Unit
		Min	Max	Min	Max	<u> </u>
Address Valid to Address Don't Care (Cycle Time when Chip Enable is Held Active)	[†] AVAX	55	_	70	_	ns
Chip Enable Low to Chip Enable High	[†] ELEH	55	<u> </u>	70		ns
Address Valid to Output Valid (Access)	tAVQV	_	55		70	ns
Chip Enable Low to Output Valid (Access)	t _{ELQV}	_	55		70	ns
Address Valid to Output Invalid	tAVQX	5		5	_	ns
Chip Enable Low to Output Invalid	tELQX_	10	_	10	_	ns
Chip Enable High to Output High Z	[‡] EHQZ	0	40	0	40	ns
Chip Selection to Power-Up Time	tėu	0	_	0	_	ns
Chip Deselection to Power-Down Time	tPD	0	30	0	30	ns
Address Valid to Chip Enable Low (Address Setup)	†AVEL	0		0		ns
Chip Enable Low to Write High	^t ELWH	45	_	55	_	ns
Address Valid to Write High	^t AVWH	45	_	55	_	ns
Address Valid to Write Low (Address Setup)	†AVWL	0		0		ns
Write Low to Write High (Write Pulse Width)	tWLWH	35	_	40	_	ns
Write High to Address Don't Care	tWHAX	10	_	15	_	ns
Data Valid to Write High	tDVWH	25	_	30	_	ns
Write High to Data Don't Care (Data Hold)	tWHDX	10		10	_	ns
Write Low to Output High Z	tWLQZ	0	30	0	35	ns
Write High to Output Valid	tWHQV	0		0		ns

TIMING PARAMETER ABBREVIATIONS

signal name from which interval is defined _____ signal name to which interval is defined _____ signal name to which interval is defined _____ transition direction for second signal _____

The transition definitions used in this data sheet are:

H = transition to high

L = transition to low

V = transition to valid

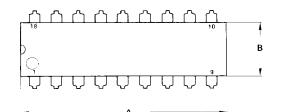
X = transition to invalid or don't care

Z = transition to off (high impedance)

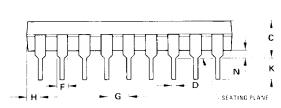
TIMING LIMITS

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

PACKAGE DIMENSIONS



P PACKAGE PLASTIC CASE 707-02





NOTES:

- 1. POSITIONAL TOLERANCE OF LEADS (D), SHALL BE WITHIN 0.25mm(0.010) AT MAXIMUM MATERIAL CONDITION, IN RELATION TO SEATING PLANE AND EACH OTHER.
- 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	MILLIN	MILLIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	22.22	23.24	0.875	0.915
В	6.10	6.60	0.240	0.260
C	3.56	4.57	0.140	0.180
D	0.36	0.56	0.014	0.022
F	1.27	1.78	0.050	0.070
G	2.54 BSC		0.100 BSC	
Н	1.02	1.52	0.040	0.060
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62	BSC	0.300 BSC	
M	00	15°	00	15 ⁰
N	0.51	1.02	0.020	0.040

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